EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	3481	(257/328-334).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/25 12:28
L4	311	L3 and (@pd>="20060901")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:29
L5	770	"vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:30
L6	623	L5 and (@ad<="20030724" or @rlad<="20030724")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:31
L7	135	("vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:33

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	3481	(257/328-334).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/25 12:28
L4	311	L3 and (@pd>="20060901")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:29
L5	770	"vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:30
L6	623	L5 and (@ad<="20030724" or @rlad<="20030724")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:31
L7	135	("vertical field effect transistor" or (vertical adj field adj effect adj trnasistor) or (vertical adj junction adj field adj effect adj trnasistor)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:33